

# **HD74CBT1G126**

# Single FET Bus Switch

REJ03D0816-0100

(Previous: ADE-205-661)

Rev.1.00 Apr 07, 2006

#### **Description**

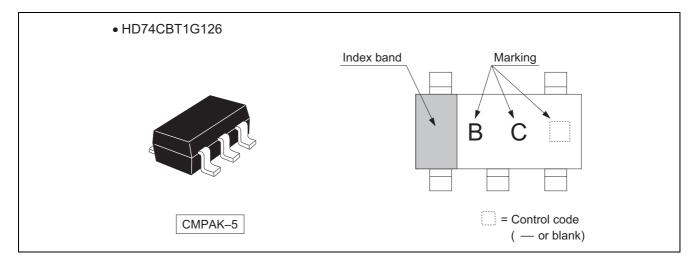
The HD74CBT1G126 features a single high-speed line switch. The switch is disabled when the output enable (OE) input is low.

#### **Features**

- Minimal propagation delay through the switch.
- $5 \Omega$  switch connection between two ports.
- TTL-compatible input levels.
- Ultra low quiescent power.
  - Ideally suited for notebook applications.
- Ordering Information

Part Name	Package Type	Package Code (Previous code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74CBT1G126CME		PTSP0005ZC-A (CMPAK-5V)	СМ	E (3,000pcs / Reel)

#### **Outline and Article Indication**

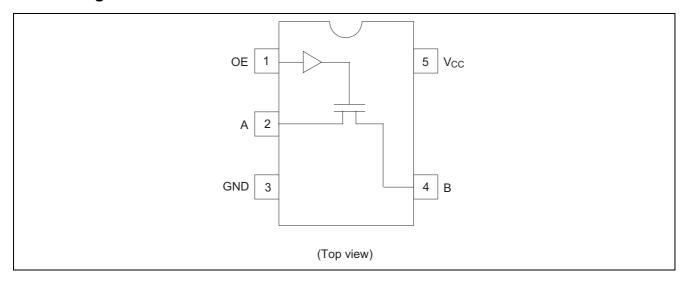


#### **Function Table**

Input OE	Function
Н	A port = B port
L	Disconnect

H: High level L: Low level

### **Pin Arrangement**



# **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V	
Input voltage range *1	Vı	-0.5 to 7.0	V	
Input clamp current	I <sub>IK</sub>	-50	mA	V <sub>I</sub> < 0
Continuous output current	I <sub>O</sub>	128	mA	$V_O = 0$ to $V_{CC}$
Continuous current through V <sub>CC</sub> or GND	I <sub>CC</sub> or I <sub>GND</sub>	±100	mA	
Maximum power dissipation at Ta = 25°C (in still air) *2	P <sub>T</sub>	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded even if the input and output clamp-current ratings are observed.
- 2. The maximum package power dissipation was calculated using a junction temperature of 150°C.

# **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V <sub>CC</sub>	4.0	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	V <sub>I/O</sub>	0	5.5	V	
Input transition rise or fall rate	Δt / Δν	0	5	ns / V	V <sub>CC</sub> = 4.5 to 5.5 V
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

#### **DC Electrical Characteristics**

 $(Ta = -40 \text{ to } 85^{\circ}C)$ 

Item	Symbol	V <sub>CC</sub> (V)	Min	Typ *1	Max	Unit	Test conditions
Clamp diode voltage	V <sub>IK</sub>	4.5	_	_	-1.2	V	$I_{IN} = -18 \text{ mA}$
Input voltage	V <sub>IH</sub>	4.0 to 5.5	2.0	_	_	V	
	V <sub>IL</sub>	4.0 to 5.5	_	_	0.8		
On-state switch resistance *2	Ron	4.0	_	14	20	Ω	$V_{IN} = 2.4 \text{ V}, I_{IN} = 15 \text{ mA}$ Typ at $V_{CC} = 4.0 \text{ V}$
		4.5		5	7		V <sub>IN</sub> = 0 V, I <sub>IN</sub> = 64 mA
		4.5	_	5	7		V <sub>IN</sub> = 0 V, I <sub>IN</sub> = 30 mA
		4.5		10	15		$V_{IN} = 2.4 \text{ V}, I_{IN} = 15 \text{ mA}$
Input current	I <sub>IN</sub>	0 to 5.5		_	±1.0	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Off-state leakage current	loz	5.5		_	±1.0	μΑ	$0 \le A, B \le V_{CC}$
Quiescent supply current	Icc	5.5	_	_	1.0	μΑ	$V_{IN} = V_{CC}$ or GND, $I_O = 0$ mA
Increase in I <sub>CC</sub> per input *3	Δlcc	5.5	_	_	2.5	mA	One input at 3.4 V, other inputs at V <sub>CC</sub> or GND

Notes: For condition shown as Min or Max use the appropriate values under recommended operating conditions.

- 1. All typical values are at  $V_{CC} = 5 \text{ V}$  (unless otherwise noted),  $Ta = 25^{\circ}C$ .
- 2. Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower voltage of the two (A or B) terminals.
- 3. This is the increase in supply current for each input that is at the specified TTL voltage level rather than  $V_{CC}$  or GND.

# Capacitance

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	Test conditions
Control input capacitance	C <sub>IN</sub>	5.0	_	3	_	pF	V <sub>IN</sub> = 0 or 3 V
Input / output capacitance	C <sub>I/O (OFF)</sub>	5.0	_	5	_	pF	$V_O = 0$ or 3 V, $OE = V_{CC}$

Note: This parameter is determined by device characterization is not production tested.

### **Switching Characteristics**

 $(Ta = -40 \text{ to } 85^{\circ}C)$ 

 $V_{CC} = 4.0 \text{ V}$ 

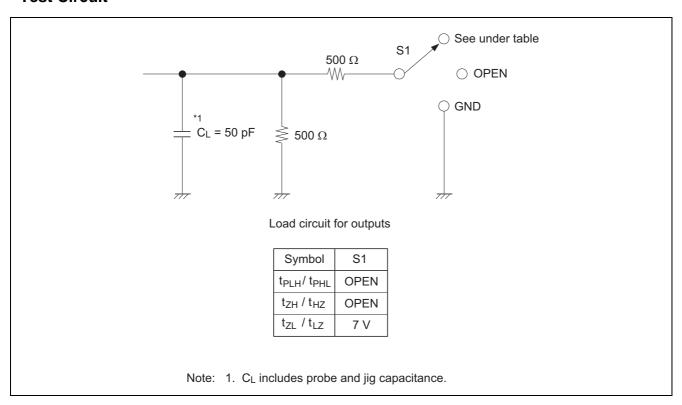
Item	Symbol	Min	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time *1	t <sub>PLH</sub>	_	0.35	ns	$C_L = 50 \text{ pF}$	A or B	B or A
	t <sub>PHL</sub>				$R_L = 500 \Omega$		
Enable time	t <sub>zH</sub>	_	5.5	ns	$C_L = 50 \text{ pF}$	OE	A or B
	$t_{ZL}$				$R_L = 500 \Omega$		
Disable time	t <sub>HZ</sub>		4.5	ns	C <sub>L</sub> = 50 pF	OE	A or B
	$t_{LZ}$		4.5		$R_L = 500 \Omega$		

 $V_{CC} = 5.0 \pm 0.5 \text{ V}$ 

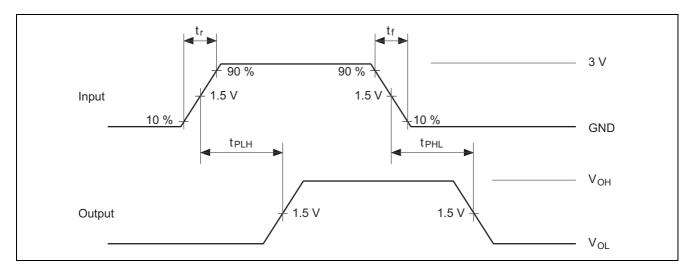
Item	Symbol	Min	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time *1	t <sub>PLH</sub>	_	0.25	ns	$C_L = 50 \text{ pF}$	A or B	B or A
	t <sub>PHL</sub>				$R_L = 500 \Omega$		
Enable time	$t_{ZH}$	1.6	4.9	ns	$C_L = 50 \text{ pF}$	OE	A or B
	$t_{ZL}$				$R_L = 500 \Omega$		
Disable time	t <sub>HZ</sub>	1.0	4.2	ns	C <sub>L</sub> = 50 pF	OE	A or B
	$t_{LZ}$	1.0	4.8		$R_L = 500 \Omega$		

Note: 1. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

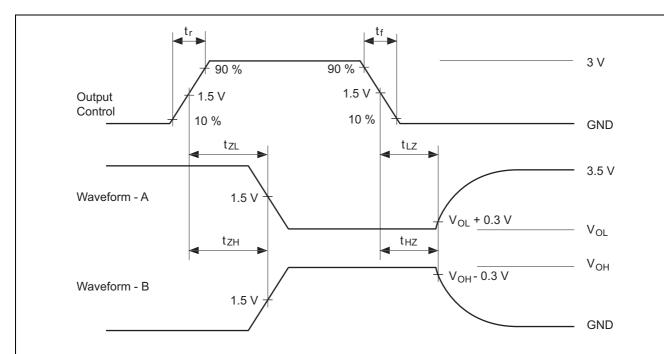
#### **Test Circuit**



#### Waveforms - 1



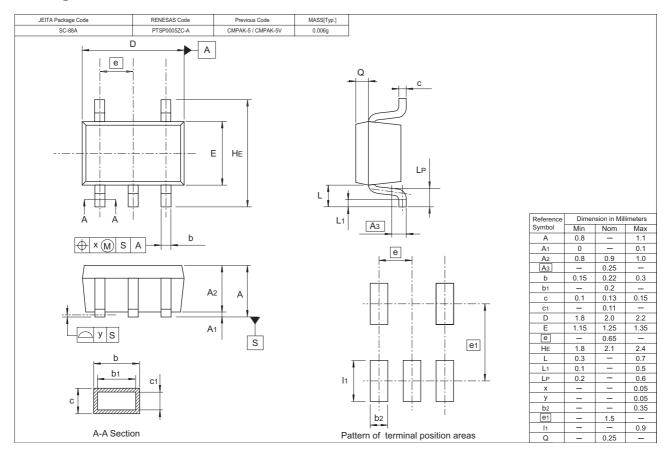
#### Waveforms - 2



Notes: 1. All input pulses are supplied by generators having the following characteristics : PRR  $\leq$  10 MHz,  $Z_O$  = 50  $\Omega$ ,  $t_r \leq$  2.5 ns,  $t_f \leq$  2.5 ns.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

# **Package Dimensions**



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